

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No
Filing Date June 11, 1999
Inventor Klaus Florian Schuegraf et al.
Assignee Micron Technology, Inc.
Group Art Unit
Examiner Ron E. Pompey
Attorney's Docket No
Title: Methods for Forming Wordlines, Transistor Gates, and Conductive Interconnects, and Wordline, Transistor Gate, and Conductive Interconnect Structures

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. No admission is made regarding whether any of the submitted references is prior art. Copies of the references are attached.

Respectfully Submitted:

Dated: 3 - 13 - 02

D. Brent Kenady Reg. No. 40,045

03/20/2002 JBALINAN 00000070 09332271

01 FC:126

180.00 DP



U.S. DEPARTMENT OF DWARCE PATENT AND TRADEMARKS FFIRE Form PTO-1449 ATTY. DOCKET NO. SERIAL NO. 09/332,271 LIST OF ART CITED BY APPLICANT APPLICANT MAR 1 4 2002 (Use several sheets if necessary) Klaus Florian Schuegraf FILING DATE GROUP June 11, 1999 2812 *Examiner Document Date Name Class Subclass Filing Date Initial Number If Appropriate 4,354,309 AA 10/1982 Gardiner et al. AB 4,559,091 12/1985 Allen et al. 148 174 AC 4,886,765 12/1989 Chen et al. 437 200 5,192,708 AD 03/1993 Beyer et al. 90 ΑE 5,393,676 02/1995 Anjum et al. 437 24 AF 5,712,181 01/1998 Byun et al. 437 46 AG 5,798,296 08/1998 Fazan et al. 438 592 ΑH 5,811,343 09/1998 Wann et al. 438 305 5,985,720 ΑI 11/1999 Saitoh 438 266 ΑJ 6,040,238 03/2000 Yang et al. 438 592 ΑK 5,164,333 11/1992 Schwalke et al. 437 200 AL FOREIGN PATENT DOCUMENTS Document Date Country Class Subclass Translation Number Yes No AM JP 02265248 A 04/1989 Japan - Kuriyama, Hiroko AN ΑO ΑP ΑQ OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) AR AS AT **EXAMINER** DATE CONSIDERED *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-14	149		U.S PA	I. DEPARTING	VA OP COMMERCE BADEMARK OFFICE	ATTI. CKET .	NO.	SERI. Unkn	IAL NO.		
		LIST OF ART CITED	D BY APPL	LICANT	(B)	APPLICANT Klaus Florian Schi			own_		
		(Use several sheets	if necessary,	(MI	MAR 1 LUUL 33	FILING DATE Filed herewith	uegraj et ai	GRO! Unkni			
				v.SQ	TE YARBEMANTS			- Uma.	ЭМП		
*Examiner Initial		Document Number	Date	Date Name			Class	Subclass		g Daie propriate	
	AA	5,425,392	06/95	Thakur et d	al.						
	AB										
	AC										
	AD				***				 		
	AE				7.74 - 77 144	· · · · · · · · · · · · · · · · · · ·			·		
	AF					·	†				
: :	AG					·					
	AH						 				
	Al										
	AJ										
	AK					-					
				FOREIGN	I PATENT DOCUMENT	rs					
ļ		Document Number	Date		Country	Country		Subclass		slation .	
	AL						+		Yes	No	
		. от	HER REFERE	NCES (includi	ling Author, Title, Date,	Pertinent Pages, Etc.	ມ 				
	AK	Taishi Kubota et al.	Taishi Kubota et al.; "The Effect of the Floating Gate/Tunnel SiO, Interface on FLASH Memory Data Retention Reliability"; 1994; 2 pages								
	AL	Shoue Jen Wang et	al.; "Effects of	f Poly Depletic	ion on the Estimate of T	Thin Dielectric Lifetin	ne"; IEEE Ele	ctron Device L	etters, Vol. 12	!, No. 11,	
		November 1991; pp.	. 617-619								
	A.M	Klaus F. Schuegraf	et al.; "Impact	of Polysilicon	n Depletion in Thin Oxi	ide MOS Technology"	'; 1993; pp. 80	5-88			
											
	AN	E. H. Snow et al.;	*Polarization P	henomena and	d Other Properties of P	hosphosilicate Glass i	Films on Silice	on"; Journal of	the Electroch	iemical	
		Society, March 1966	Society, March 1966; pp. 263-269								
EXAMINER	EXAMINER					ED.					
*EXAMINER: Include copy of	Initial if n f this form	reference considered, whether or with next communication to ap	r not citation i applicant.	is in conforma	Ince with MPEP 609; L)raw line through cita	ition if not in	conformance a	and not consid	lered.	

EV026157368

